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P. 14/17

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant: Zhu et al.	
(Use Several Sheets if Necessary)	Filing Date December 10, 2003	Group 2891

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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant: Zhu et al.	
(Use Several Sheets if Necessary)	Filing Date December 10, 2003	Group 2891

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Form 1449 (Modified)	Atty Docket No. NOVLP090/NVLS-2888	Application No.: 10/733,858
Information Disclosure Statement By Applicant	Applicant: Zhu et al. Filing Date	Group
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Form 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888 Application No.: 10/733,858

Information Disclosure Statement By Applicant

Applicant: Zhu et al. Filing Date

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Examiner: Initial citation considered. Draw line through citation if not in conformance and not

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ogn 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888

Application No.:

Information Disclosure Statement By Applicant Applicant: Zhu et al.

10/733,858

(Use Several Sheets if Necessary)

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Foreign Patent or Published Foreign Patent Application

Examiner		Document	Publication	Country or		Sub-	Trans	lation
Initial	No.	No.	Date	Patent Office	Class	class	Yes	No
	B1	JP 2003-031,649	01.2003	Japan				

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		Other Documents			
Examiner					
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication			
-1111	C1	U.S. Office Action mailed August 6, 2003, from U.S. Application No. 10/058,897.			
75/5		[Atty Dckt. NOVLP040X1/NVLS-000607]			
C2 U.S. Office Action mailed January 29, 2004, from U.S. Application No. 1					
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\		High Aspect Ratio Structures", Novellus Systems, Inc., filed October 11, 2002,			
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Other Documents

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<u> </u>		No. 10/991,890, pages 1-35. [Atty Dkt No. NOVLP119/NVLS-2988]
Examiner		Date Considered
	15_1	3/19/06

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Form 1449 (Modified)

Atty Docket No. NOVLP090/NVLS-2888

Application No.: 10/733,858

Information Disclosure Statement By Applicant Applicant: Zhu et al.

(Use Several Sheets if Necessary)

Filing Date
December 10, 2003

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Other Documents

		Other Documents
Examiner		
Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BKS	C29	[Atty Dckt. NOVLP113/NVLS-2949]
BKS BKS	C30	Lang et al., "Using Water (H20) To Replace Oxygen (02) In A Silicon Dioxide (Si02) Thin Film Deposition Process for HDP STI Technology", Novellus Systems, Inc., filed November 9, 2005, Application No. 11/272,487, pages 1-25. [Atty Dkt No. NOVLP136/NVLS-3082].
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